

<b>SANYO</b>	No.3485	<b>2SC4694</b>
		NPN Epitaxial Planar Silicon Transistor <b>Low-Frequency General-Purpose Amp, Muting Applications</b>

**Features**

- Adoption of FBET process
- High DC current gain
- High  $V_{EBO}$  ( $V_{EBO} \geq 25V$ )
- High reverse  $h_{FE}$  (150 typ)
- Small ON resistance [ $R_{on} = 1\Omega$  ( $I_B = 5mA$ )]
- Very small-sized package permitting 2SC4694-applied sets to be made small and slim

**Absolute Maximum Ratings at  $T_a = 25^\circ C$**

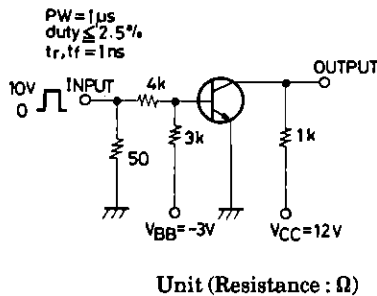
			unit
Collector to Base Voltage	$V_{CBO}$	50	V
Collector to Emitter Voltage	$V_{CEO}$	20	V
Emitter to Base Voltage	$V_{EBO}$	25	V
Collector Current	$I_C$	500	mA
Collector Current(Pulse)	$I_{CP}$	800	mA
Base Current	$I_B$	100	mA
Collector Dissipation	$P_C$	150	mW
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	- 55 to + 150	$^\circ C$

**Electrical Characteristics at  $T_a = 25^\circ C$**

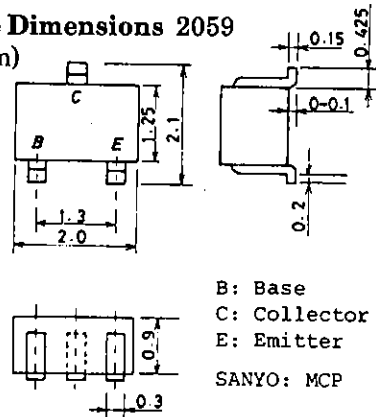
			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 40V, I_E = 0$			0.1	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 20V, I_C = 0$			0.1	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE} = 5V, I_C = 10mA$	300		1200	
Gain-Bandwidth Product	$f_T$	$V_{CE} = 10V, I_C = 10mA$		250		MHz
Output Capacitance	$c_{ob}$	$V_{CB} = 10V, f = 1MHz$		3.6		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 100mA, I_B = 2mA$		0.12	0.5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 100mA, I_B = 2mA$		0.85	1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	50			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA, I_B = 0$	20			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	25			V
Turn-ON time	$t_{on}$	See specified Test Circuit.		135		ns
Storage Time	$t_{stg}$	See specified Test Circuit.		450		ns
Fall Time	$t_f$	See specified Test Circuit.		100		ns

Marking : WT

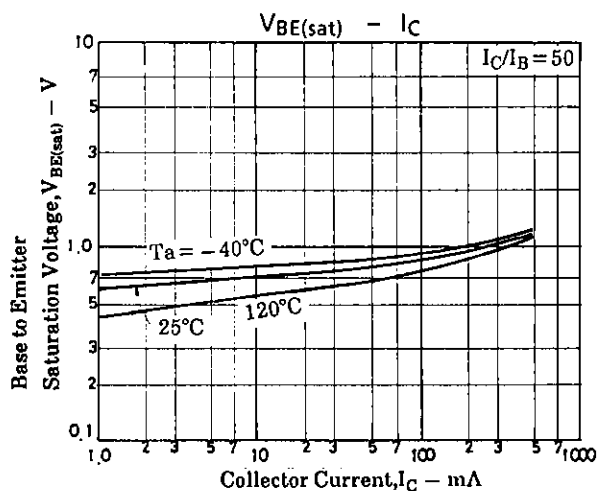
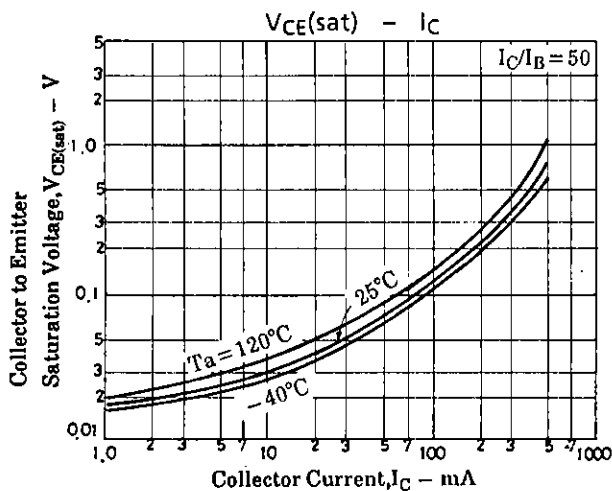
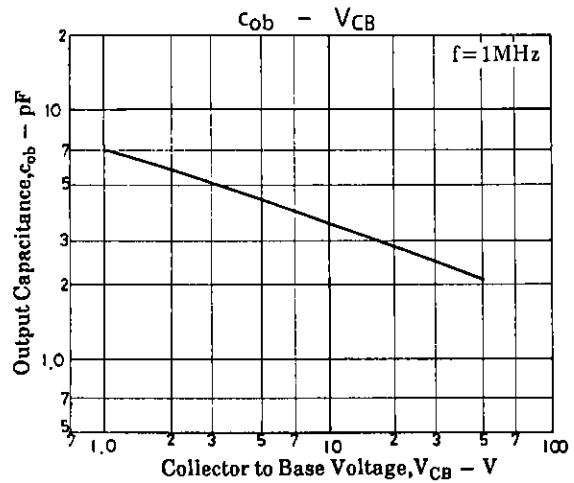
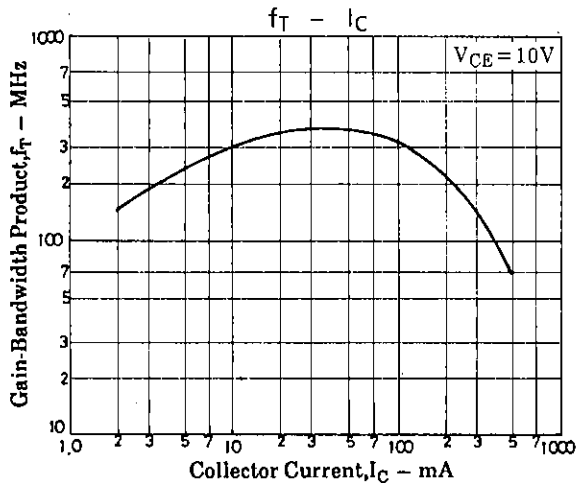
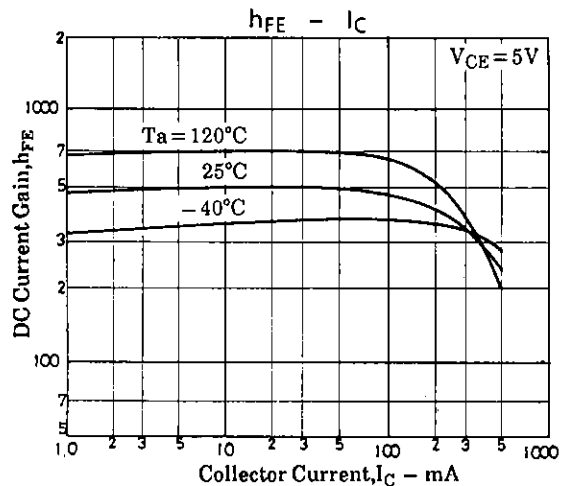
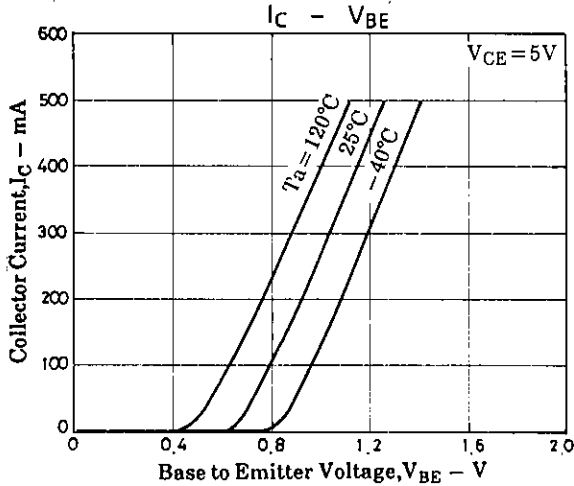
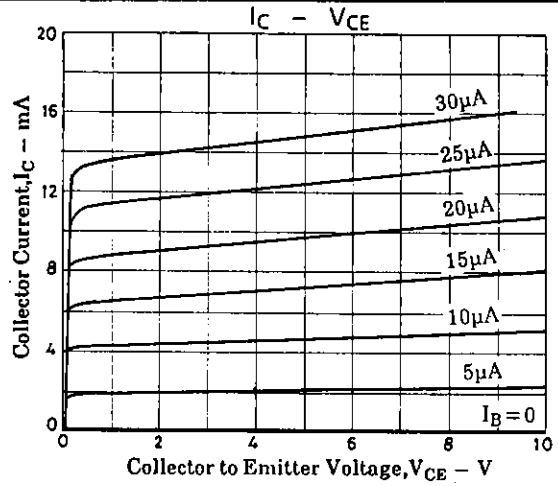
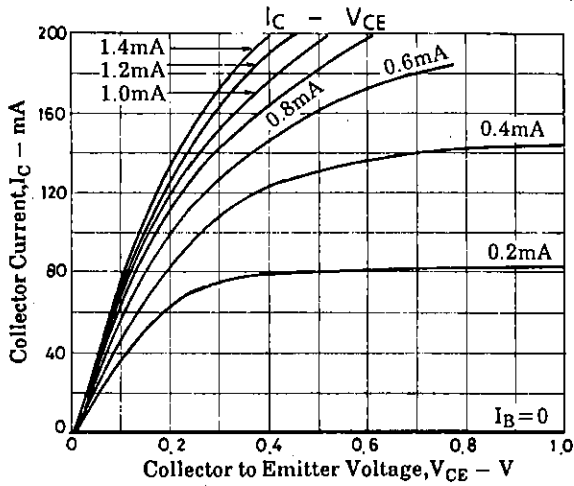
**Switching Time Test Circuit**

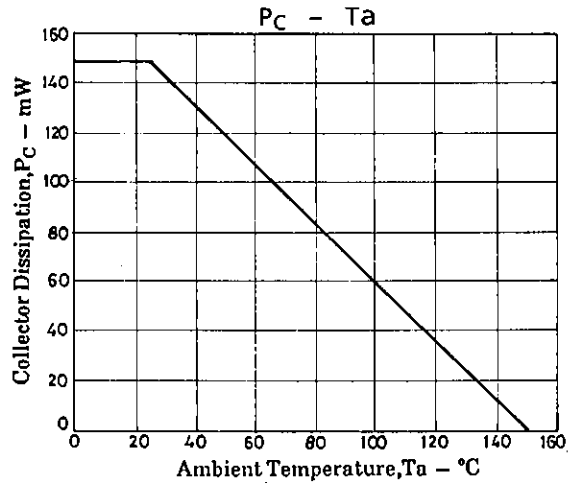
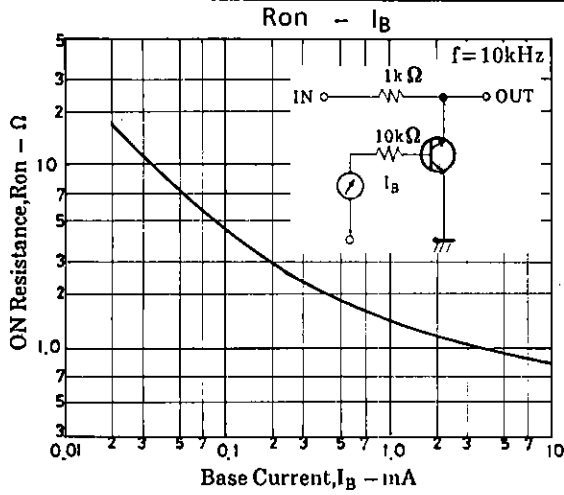


**Package Dimensions 2059**  
(unit : mm)



2SC4694





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